



Surface Mount Super Fast Recovery Rectifier

Features

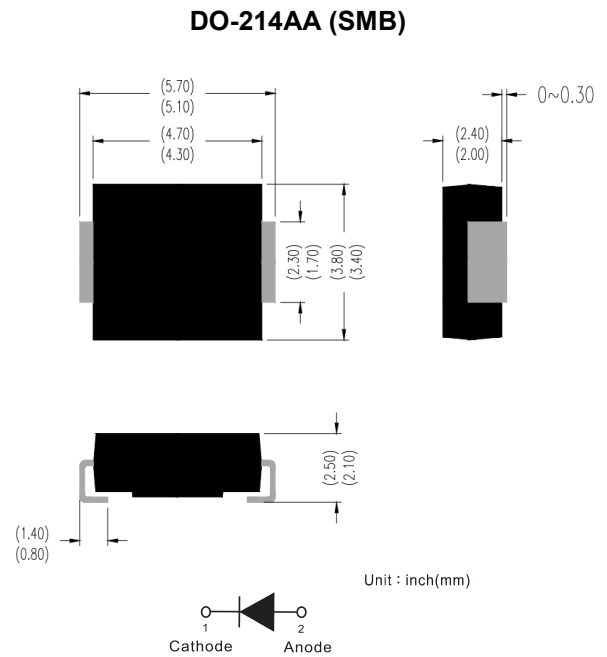
- Low profile package
- Ideal for automated placement
- Glass passivated chip junction
- High forward surge capability
- Super Fast reverse recovery time
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

Typical Applications

For use in high frequency rectification of power supplies, inverters, converters, and freewheeling diodes for consumer, and telecommunication.

Mechanical Data

- **Package:** DO-214AA (SMB)
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free
- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD22-B102
- **Polarity:** Cathode line denotes the cathode end



■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MURS120	MURS140	MURS160
Maximum Repetitive Peak Reverse Voltage	VRRM	V	200	400	600
Maximum RMS Voltage	VRMS	V	140	280	420
Maximum DC blocking Voltage	VDC	V	200	400	600
Average rectified output current @60Hz sine wave, resistance load, TL (Fig.1)	IO	A	1.0		
Forward Surge Current (Non-repetitive) @60Hz Half-sine wave, 1 cycle, Tj=25°C	IFSM	A	30		
Forward Surge Current (Non-repetitive) @1ms, square wave, 1 cycle, Tj=25°C			60		
Current squared time @1ms≤t≤8.3ms Tj=25°C	I²t	A²s	3.735		
Storage temperature	Tstg	°C	-55 ~ +150		
Junction temperature	Tj	°C	-55 ~ +150		



■ Electrical Characteristics (T_a=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MURS120	MURS140	MURS160
Maximum instantaneous forward voltage	V _F	V	I _{FM} =1.0A	0.92	1.25	
Maximum reverse recovery time	t _{rr}	ns	I _F =0.5A, I _R =1.0A, I _{rr} =0.25A	25	50	
Maximum DC reverse current at rated DC blocking voltage	I _R	μA	T _j =25°C	5.0		
			T _j =125°C	50		
Typical junction capacitance	C _j	pF	Measured at 1MHz and Applied Reverse Voltage of 4.0 V.D.C	17	15	14

■ Dynamic Characteristics

◆ MURS120

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS		Min	Typ	Max
Reverse Recovery Time	T _{RR}	ns	T _j =25°C	I _F =1A, di/dt=-50A/us V _{RM} =30V	-	26	-
			T _j =25°C	I _F =1A di/dt=-200A/us V _{RM} =100V	-	18	-
			T _j =125°C		-	23	-
Peak recovery current	I _{RRM}	A	T _j =25°C	I _F =1A di/dt=-200A/us V _{RM} =100V	-	2.3	-
			T _j =125°C		-	3.8	-
Reverse recovery charge	Q _{rr}	nC	T _j =25°C	I _F =1A di/dt=-200A/us V _{RM} =100V	-	20.2	-
			T _j =125°C		-	43.7	-
Non-repetitive avalanche energy	E _{AS}	mJ	T _j =25°C	I _R =1.5 A, L=15 mH	16.9	-	-

◆ MURS140

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS		Min	Typ	Max
Reverse Recovery Time	T _{RR}	ns	T _j =25°C	I _F =1A, di/dt=-50A/us V _{RM} =30V	-	26	-
			T _j =25°C	I _F =1A di/dt=-200A/us V _{RM} =200V	-	22	-
			T _j =125°C		-	31	-
Peak recovery current	I _{RRM}	A	T _j =25°C	I _F =1A di/dt=-200A/us V _{RM} =200V	-	1.9	-
			T _j =125°C		-	3.5	-
Reverse recovery charge	Q _{rr}	nC	T _j =25°C	I _F =1A di/dt=-200A/us V _{RM} =200V	-	21.1	-
			T _j =125°C		-	54.9	-
Non-repetitive avalanche energy	E _{AS}	mJ	T _j =25°C	I _R =0.4A, L=15 mH	1.2	-	-

◆ MURS160

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS		Min	Typ	Max
Reverse Recovery Time	T _{RR}	ns	T _j =25°C	I _F =1A, di/dt=-50A/us V _{RM} =30V	-	49	-
			T _j =25°C	I _F =1A di/dt=-200A/us V _{RM} =400V	-	38	-
			T _j =125°C		-	59	-
Peak recovery current	I _{RRM}	A	T _j =25°C	I _F =1A di/dt=-200A/us V _{RM} =400V	-	3.5	-
			T _j =125°C		-	5.5	-
Reverse recovery charge	Q _{rr}	nC	T _j =25°C	I _F =1A di/dt=-200A/us V _{RM} =400V	-	67.4	-
			T _j =125°C		-	160.5	-
Non-repetitive avalanche energy	E _{AS}	mJ	T _j =25°C	I _R =0.5A, L=15 mH	1.9	-	-



■ Thermal Characteristics (T_a=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MURS120	MURS140	MURS160
Typical Thermal resistance	R θ J-A ⁽¹⁾	°C/W	65		
	R θ J-L ⁽¹⁾		20		
	R θ J-C ⁽¹⁾		18		

Note:
(1) Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.3" x 0.3" (8.0 mm x 8.0 mm) copper pad areas

■ Characteristics (Typical)

FIG.1: I_o-T_L Curve

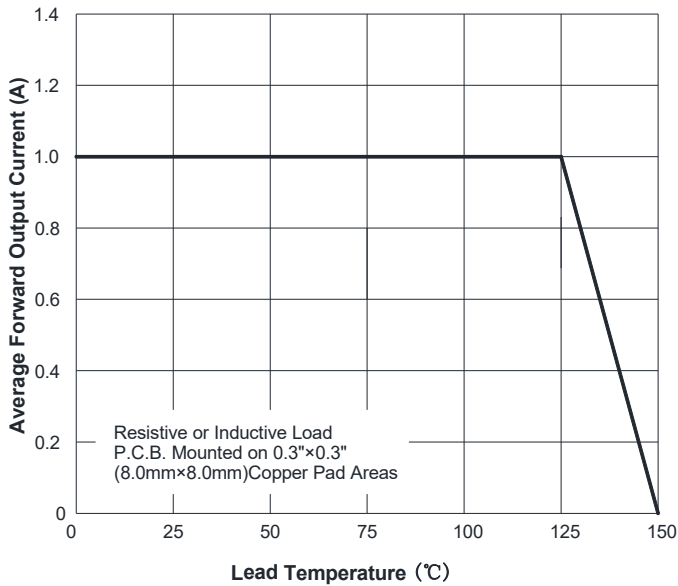


FIG.2: Forward Surge Current Capacity

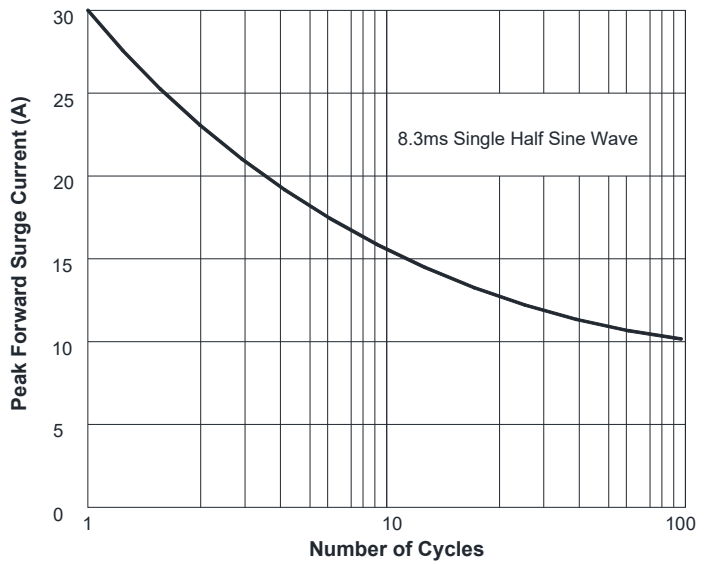


FIG.3: Typical Forward Voltage

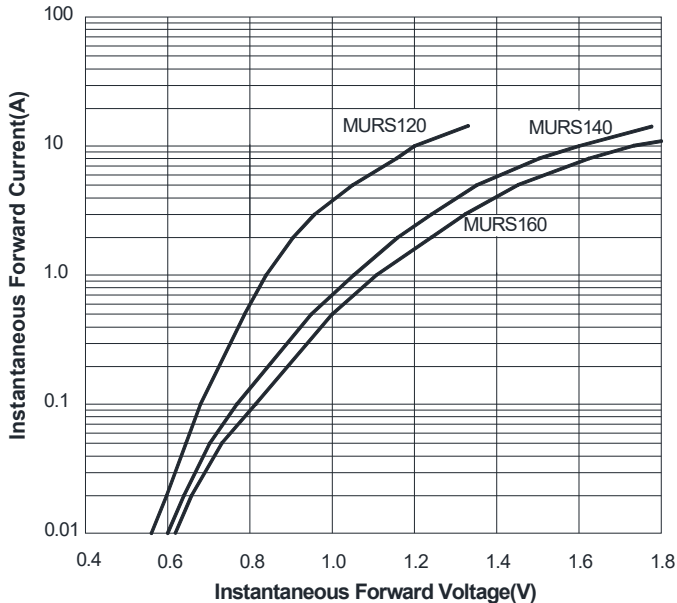


FIG.4: Typical Reverse Characteristics

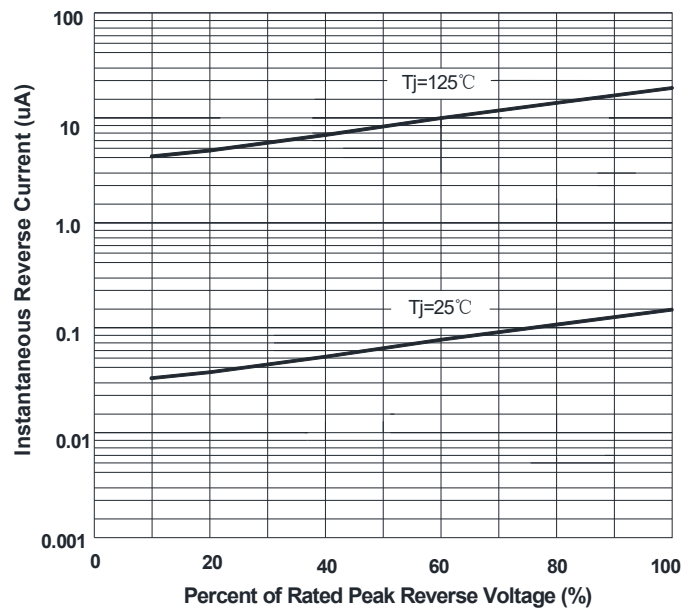




FIG.5: Diagram of circuit and Testing wave form of reverse recovery time

